

### ● General Description

The AGM608C combines advanced trenchMOSFET technology with a low resistance package to provide extremely low  $R_{DS(ON)}$ .

This device is ideal for load switch and battery protection applications.

### ● Features

- Advance high cell density Trench technology
- Low  $R_{DS(ON)}$  to minimize conductive loss
- Low Gate Charge for fast switching
- Low Thermal resistance
- 100% Avalanche tested
- 100% DVDS tested

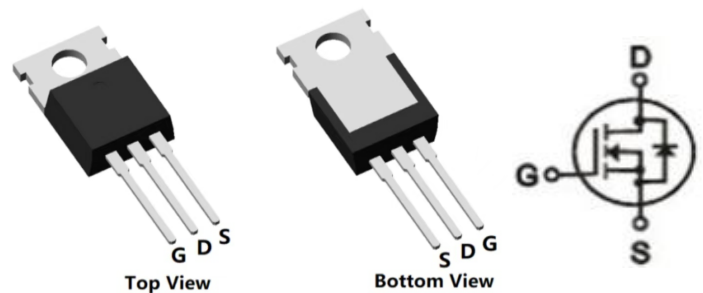
### ● Application

- MB/VGA Vcore
- SMPS 2<sup>nd</sup> Synchronous Rectifier
- POL application
- BLDC Motor driver

### Product Summary

BVDSS	RDSON	ID
60V	4.8mΩ	90A

### TO-220 Pin Configuration



### Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
AGM608C	AGM608C	TO-220	----	----	1000

**Table 1. Absolute Maximum Ratings (TA=25°C)**

Symbol	Parameter	Value	Unit
VDS	Drain-Source Voltage (VGS=0V)	60	V
VGS	Gate-Source Voltage (VDS=0V)	±20	V
ID	Drain Current-Continuous(Tc=25°C) <b>(Note 1)</b>	90	A
	Drain Current-Continuous(Tc=100°C)	61	A
IDM (pluse)	Drain Current-Continuous@ Current-Pulsed <b>(Note 2)</b>	360	A
PD	Maximum Power Dissipation(Tc=25°C)	54	w
	Maximum Power Dissipation(Tc=100°C)	22	w
EAS	Avalanche energy <b>(Note 3)</b>	92	mJ
TJ,TSTG	Operating Junction and Storage Temperature Range	-55 To 150	°C

**Table 2. Thermal Characteristic**

Symbol	Parameter	Typ	Max	Unit
RθJA	Thermal Resistance Junction-ambient (Steady State) <sup>1</sup>	---	55	°C/W
RθJC	Thermal Resistance Junction-Case <sup>1</sup>	---	2.3	°C/W

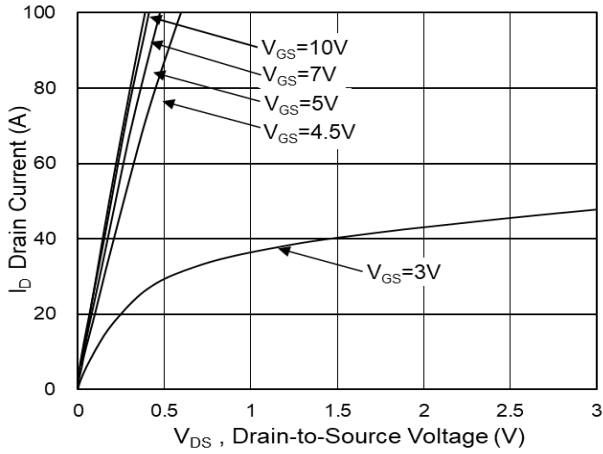
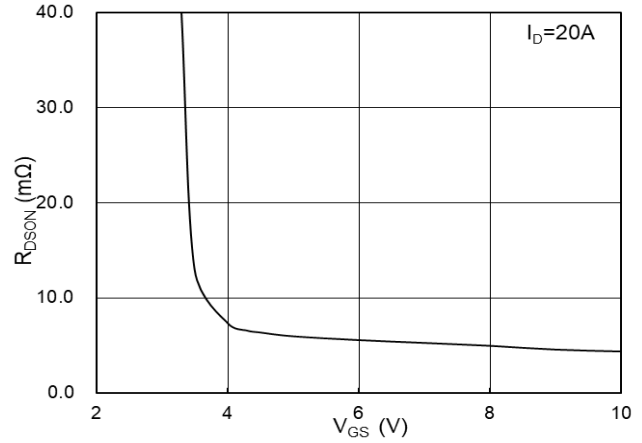
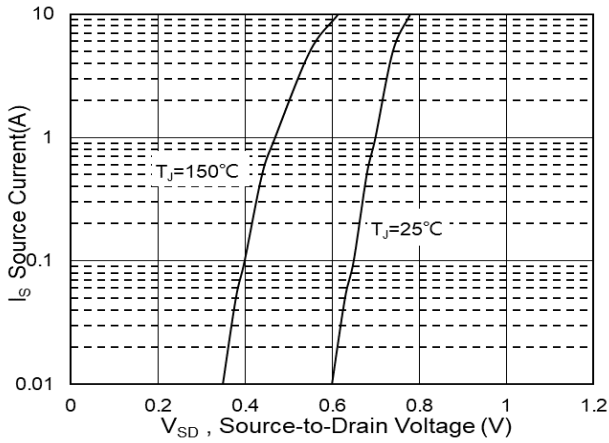
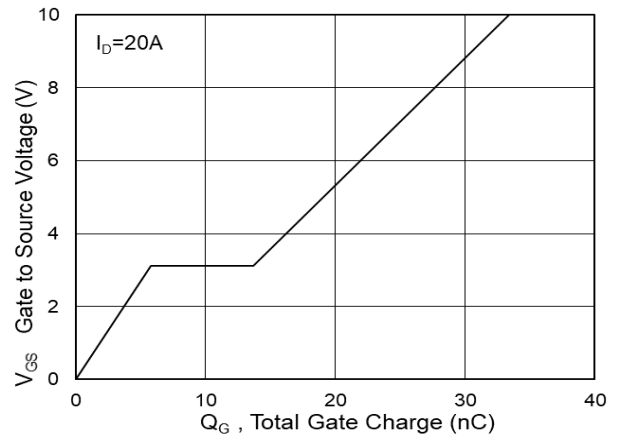
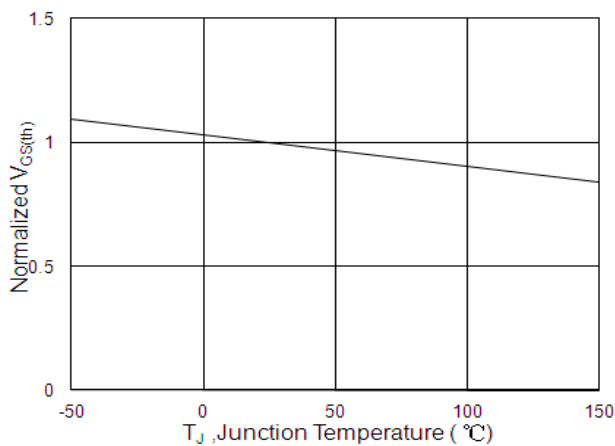
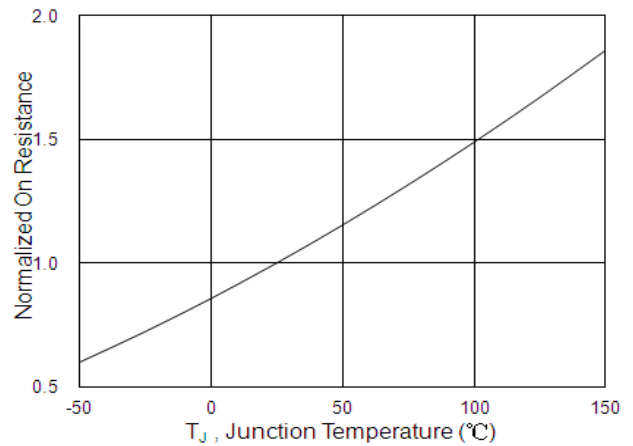
**Table 3. Electrical Characteristics (T<sub>j</sub>=25°C unless otherwise noted)**

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>On/Off States</b>						
BVDSS	Drain-Source Breakdown Voltage	VGS=0V ID=250μA	60	--	--	V
IDSS	Zero Gate Voltage Drain Current	VDS=60V, VGS=0V	--	--	1	μA
IGSS	Gate-Body Leakage Current	VGS=±20V, VDS=0V	--	--	±100	nA
VGS(th)	Gate Threshold Voltage	VDS=VGS, ID=250μA	1.2	1.6	2.1	V
gFS	Forward Transconductance	VDS=5V, ID=15A	--	10	--	S
RDS(on)	Drain-Source On-State Resistance	VGS=10V, ID=20A	--	4.8	6.5	mΩ
		VGS=4.5V, ID=15A	--	6.5	8.6	mΩ
<b>Dynamic Characteristics</b>						
Ciss	Input Capacitance	VDS=30V, VGS=0V, F=1MHZ	--	1280	--	pF
Coss	Output Capacitance		--	428	--	pF
Crss	Reverse Transfer Capacitance		--	25	--	pF
Rg	Gate resistance	VGS=0V, VDS=0V, f=1.0MHz	--	1.3	--	Ω
<b>Switching Times</b>						
td(on)	Turn-on Delay Time	VGS=10V, VDS=30V, ID=30A, RGEN=3.3Ω	--	7.5	--	nS
tr	Turn-on Rise Time		--	6.0	--	nS
td(off)	Turn-Off Delay Time		--	29	--	nS
tf	Turn-Off Fall Time		--	7.5	--	nS
Qg	Total Gate Charge	VGS=10V, VDS=30V, ID=12A	--	33	--	nC
Qgs	Gate-Source Charge		--	5.8	--	nC
Qgd	Gate-Drain Charge		--	7.9	--	nC
<b>Source-Drain Diode Characteristics</b>						
ISD	Source-Drain Current(Body Diode)		--	--	90	A
VSD	Forward on Voltage	VGS=0V, IS=20A	--	--	1.2	V
trr	Reverse Recovery Time	IF=20A , dI/dt=100A/μs , TJ=25°C	--	23	--	ns
Qrr	Reverse Recovery Charge		--	60	--	nc

Notes 1.The maximum current rating is package limited.

Notes 2.Repetitive Rating: Pulse width limited by maximum junction temperature

Notes 3.EAS condition: TJ=25°C

**Typical Characteristics**

**Fig.1 Typical Output Characteristics**

**Fig.2 On-Resistance vs G-S Voltage**

**Fig.3 Source Drain Forward Characteristics**

**Fig.4 Gate-Charge Characteristics**

**Fig.5 Normalized  $V_{GS(th)}$  vs  $T_J$** 

**Fig.6 Normalized  $R_{DS(on)}$  vs  $T_J$**

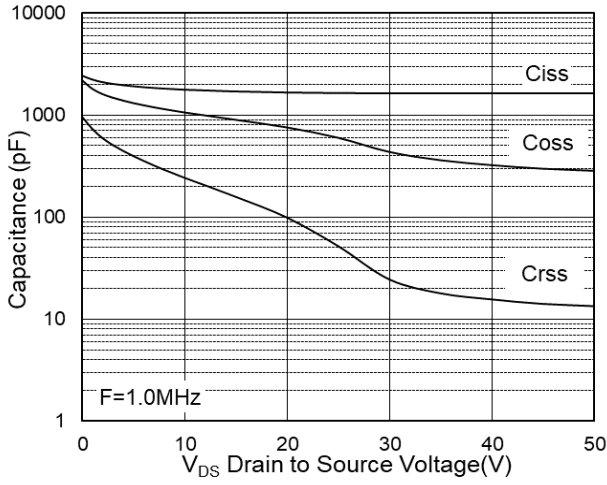


Fig.7 Capacitance

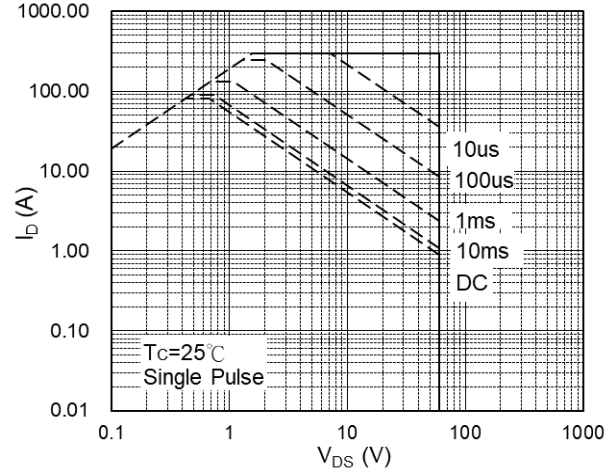


Fig.8 Safe Operating Area

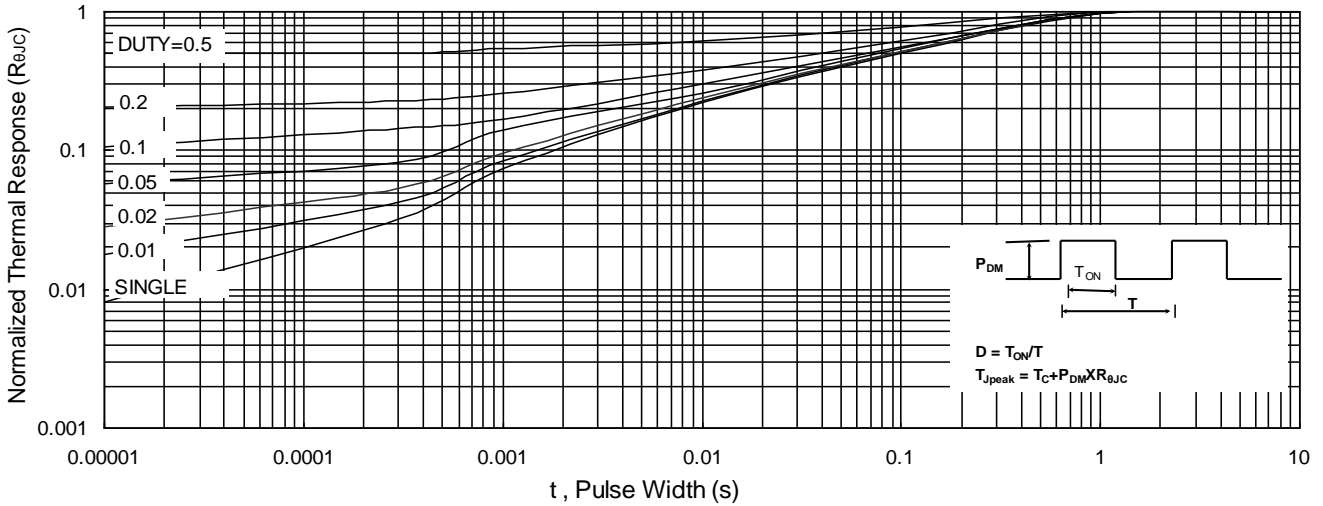


Fig.9 Normalized Maximum Transient Thermal Impedance

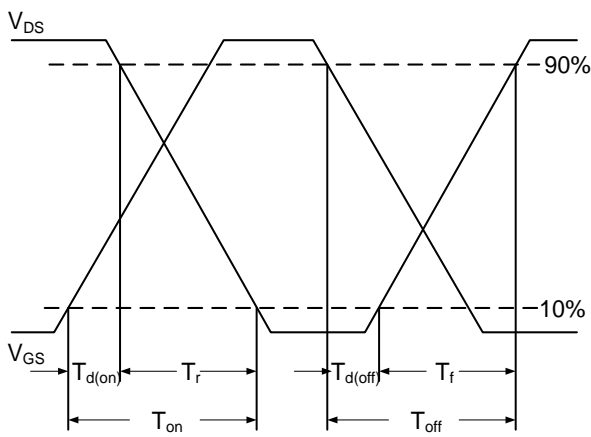


Fig.10 Switching Time Waveform

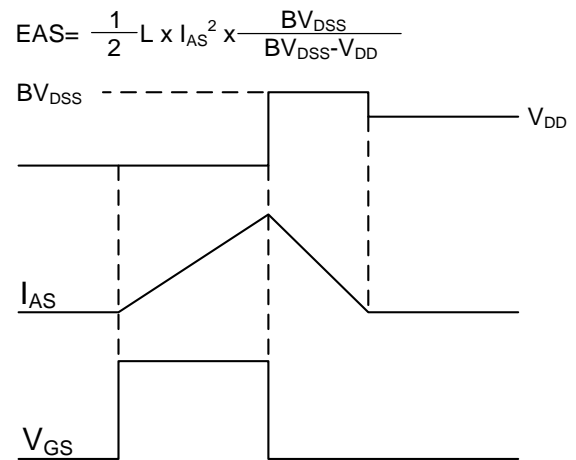
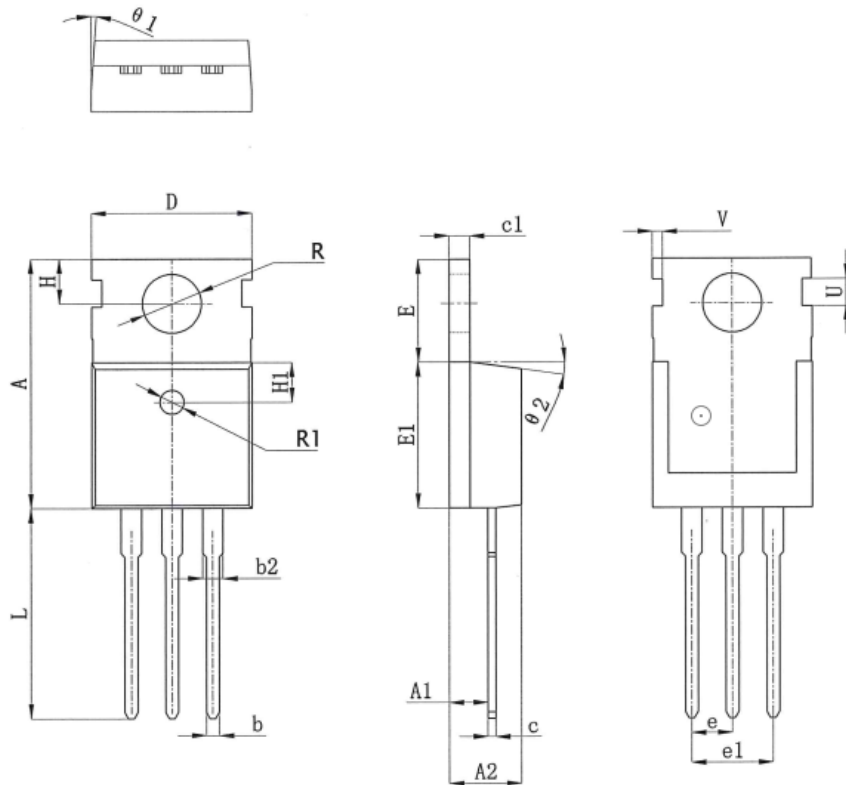
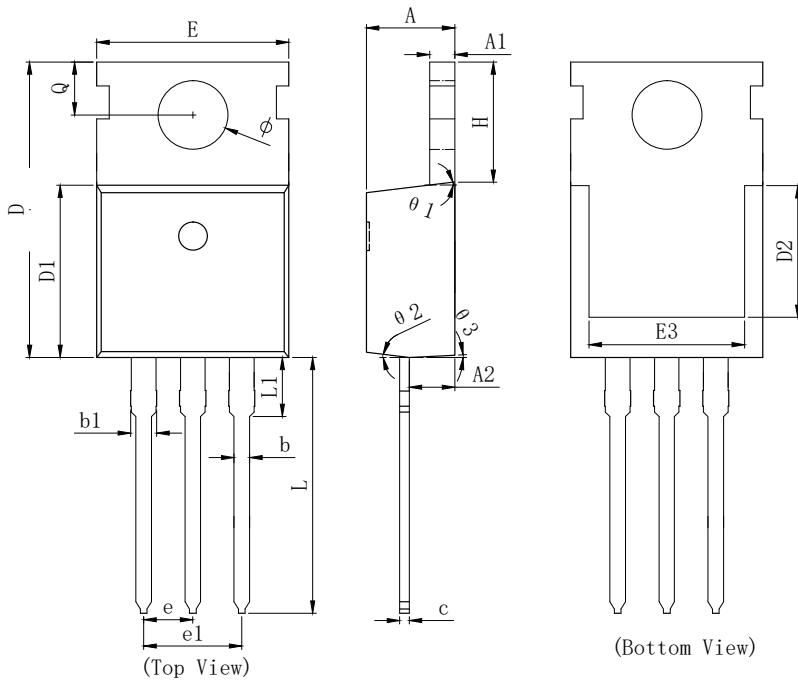


Fig.11 Unclamped Inductive Switching Waveform

# TO-220 PACKAGE INFORMATION



SYMBOL	MILLIMETER		
	MIN	NOM	MAX
A	15.400	15.600	15.800
A1	2.350	2.400	2.500
A2	4.400	4.500	4.700
b	0.700	0.800	0.900
b2	1.180	1.310	1.440
c	0.480	0.500	0.560
c1	1.290	1.300	1.320
D	9.800	10.000	10.200
E	6.400	6.500	6.600
E1	9.000	9.100	9.200
e	2.420	2.540	2.660
e1	4.840	5.080	5.320
H	2.730	2.800	2.870
H1	2.400	2.500	2.600
L	13.020	13.370	13.720
R	3.500	3.600	3.730
R1	1.400	1.500	1.600
U	1.650	1.750	1.850
V	0.580	0.680	0.780
$\theta 1$	2°	2.5°	3°
$\theta 2$	6.5°	7°	7.5°



SYMBOL	MILLIMETER		
	MIN	Typ.	MAX
A	4.370	4.570	4.700
A1	1.250	1.300	1.400
A2	2.150	2.350	2.550
b	0.700	0.800	0.950
b1	1.170	1.270	1.470
c	0.450	0.500	0.600
D	15.100	15.600	16.100
D1	8.800	9.100	9.400
D2	5.500	6.300 REF	
E	9.700	10.000	10.300
E3	7.000	7.600 REF	
e	2.540 BSC		
e1	5.080 BSC		
L	13.200	13.500	13.800
L1		3.100	3.400
H	6.250	6.500	6.750
$\phi$	3.400	3.600	3.800
Q	2.600	2.800	3.000
$\theta 1$	7° TYP		
$\theta 2$	7° TYP		
$\theta 3$	3° TYP		


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